

NX3L2G66

Low-voltage analog switch

Rev. 01 — 31 January 2008

Product data sheet

1. General description

The NX3L2G66 provides two, low-ohmic, single pole, single throw analog switch functions. Each switch has two input/output terminals (nY and nZ) and an active HIGH enable input (nE). When pin nE is LOW, the analog switch is turned off.

Schmitt-trigger action at the enable input (nE) makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 1.4 V to 3.6 V.

The NX3L2G66 allows signals with amplitude up to V_{CC} to be transmitted from nY to nZ; or from nZ to nY. Its low ON resistance (0.5 Ω) and flatness (0.13 Ω) ensures minimal attenuation and distortion of transmitted signals.

2. Features

- Wide supply voltage range from 1.4 V to 3.6 V
- Very low ON resistance (peak):
 - ◆ 1.6 Ω (typical) at $V_{CC} = 1.4$ V
 - ◆ 1.0 Ω (typical) at $V_{CC} = 1.65$ V
 - ◆ 0.55 Ω (typical) at $V_{CC} = 2.3$ V
 - ◆ 0.50 Ω (typical) at $V_{CC} = 2.7$ V
- High noise immunity
- ESD protection:
 - ◆ HBM JESD22-A114E Class 3A exceeds 7500 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM AEC-Q100-011 revision B exceeds 1000 V
- CMOS low-power consumption
- Latch-up performance exceeds 100 mA per JESD 78 Class II Level A
- Direct interface with TTL levels at 3.0 V
- Control input accepts voltages above supply voltage
- High current handling capability (350 mA continuous current under 3.3 V supply)
- Specified from -40 °C to $+85$ °C and from -40 °C to $+125$ °C

3. Applications

- Cell phone
- PDA
- Portable media player

4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
NX3L2G66GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1
NX3L2G66GM	-40 °C to +125 °C	XQFN8U	plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 × 1.6 × 0.5 mm	SOT902-1

5. Marking

Table 2. Marking

Type number	Marking code
NX3L2G66GT	D66
NX3L2G66GM	D66

6. Functional diagram

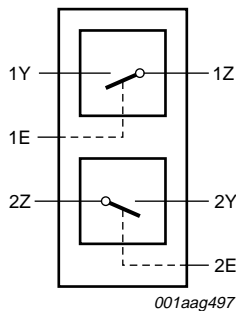


Fig 1. Logic symbol

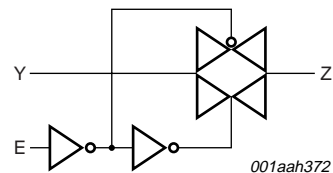


Fig 2. Logic diagram (one switch)

7. Pinning information

7.1 Pinning

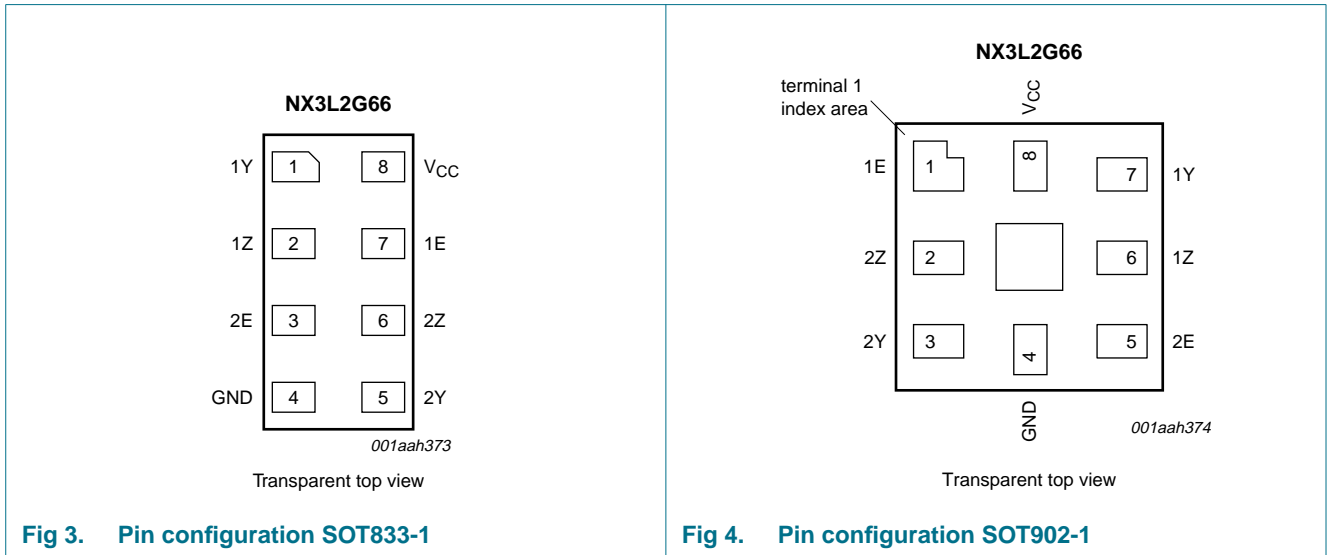


Fig 3. Pin configuration SOT833-1

Fig 4. Pin configuration SOT902-1

7.2 Pin description

Table 3. Pin description

Symbol	Pin		Description
	SOT833-1	SOT902-1	
1Y	1	7	independent input or output
1Z	2	6	independent input or output
2E	3	5	enable input (active HIGH)
GND	4	4	ground (0 V)
2Y	5	3	independent input or output
2Z	6	2	independent input or output
1E	7	1	enable input (active HIGH)
V _{CC}	8	8	supply voltage

8. Functional description

Table 4. Function table^[1]

Input nE	Switch
L	OFF-state
H	ON-state

[1] H = HIGH voltage level;
L = LOW voltage level.

9. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
V_I	input voltage		[1] -0.5	+4.6	V
V_{SW}	switch voltage		[2] -0.5	$V_{CC} + 0.5$	V
I_{IK}	input clamping current	$V_I < -0.5$ V	-50	-	mA
I_{SK}	switch clamping current	$V_I < -0.5$ V or $V_I > V_{CC} + 0.5$ V	-	± 50	mA
I_{SW}	switch current	$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; source or sink current	-	± 350	mA
		$V_{SW} > -0.5$ V or $V_{SW} < V_{CC} + 0.5$ V; pulsed at 1 ms duration, < 10 % duty cycle; peak current	-	± 500	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[3] -	250	mW

[1] The minimum input voltage rating may be exceeded if the input current rating is observed.

[2] The minimum and maximum switch voltage ratings may be exceeded if the switch clamping current rating is observed.

[3] For XSON8 and XQFN8U packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.4	-	3.6	V
V_I	input voltage	enable input nE	0	-	3.6	V
V_{SW}	switch voltage		[1] 0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.4$ V to 3.6 V	[2] -	-	200	ns/V

[1] To avoid sinking GND current from of terminal nZ when switch current flows in terminal nY, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal nZ, no GND current will flow from terminal nY. In this case, there is no limit for the voltage drop across the switch.

[2] Applies to control signal levels.

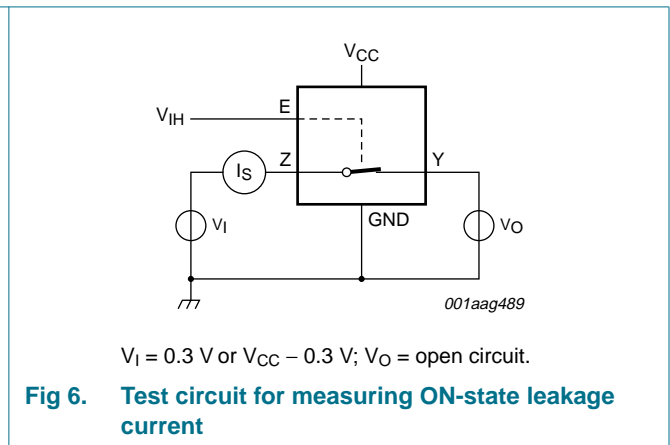
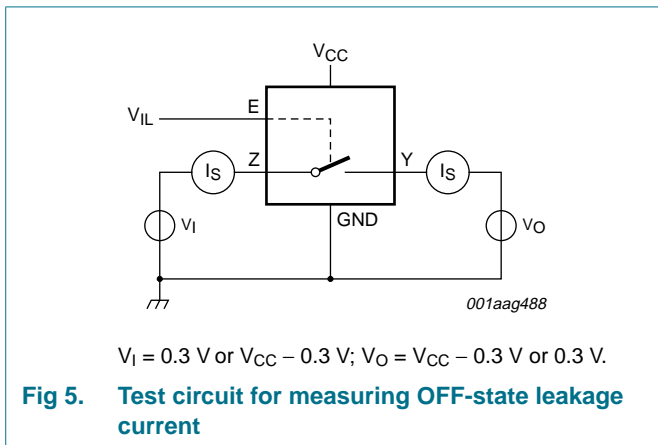
11. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground 0 V).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
V _{IH}	HIGH-level input voltage	V _{CC} = 1.4 V to 1.95 V	0.65V _{CC}	-	-	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 1.4 V to 1.95 V	-	-	0.35V _{CC}	-	0.35V _{CC}	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	0.8	V
I _I	input leakage current	enable input nE; V _I = GND to 3.6 V; V _{CC} = 1.4 V to 3.6 V	-	-	-	-	±0.5	±1	µA
I _{S(OFF)}	OFF-state leakage current	Y port; V _{CC} = 1.4 V to 3.6 V; see Figure 5	-	-	±5	-	±50	±500	nA
I _{S(ON)}	ON-state leakage current	Z port; V _{CC} = 1.4 V to 3.6 V; see Figure 6	-	-	±5	-	±50	±500	nA
I _{CC}	supply current	V _I = V _{CC} or GND; V _{CC} = 3.6 V; V _{SW} = GND or V _{CC}	-	-	100	-	690	6000	nA
C _I	input capacitance		-	1.0	-	-	-	-	pF
C _{S(OFF)}	OFF-state capacitance		-	35	-	-	-	-	pF
C _{S(ON)}	ON-state capacitance		-	110	-	-	-	-	pF

11.1 Test circuits



11.2 ON resistance

Table 8. ON resistance

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for graphs see [Figure 8](#) to [Figure 13](#).

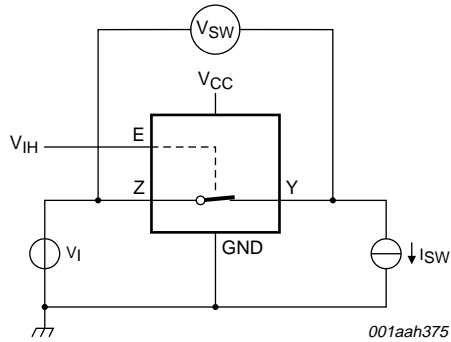
Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit	
			Min	Typ ^[1]	Max	Min	Max		
R _{ON(peak)}	ON resistance (peak)	V _I = GND to V _{CC} ; I _{SW} = 100 mA; see Figure 7							
			V _{CC} = 1.4 V	-	1.6	3.7	-	4.1	Ω
			V _{CC} = 1.65 V	-	1.0	1.6	-	1.7	Ω
			V _{CC} = 2.3 V	-	0.55	0.8	-	0.9	Ω
			V _{CC} = 2.7 V	-	0.5	0.75	-	0.9	Ω
ΔR _{ON}	ON resistance mismatch between channels	V _I = GND to V _{CC} ; I _{SW} = 100 mA							
			V _{CC} = 1.4 V	-	0.04	0.3	-	0.3	Ω
			V _{CC} = 1.65 V	-	0.04	0.2	-	0.3	Ω
			V _{CC} = 2.3 V	-	0.02	0.08	-	0.1	Ω
			V _{CC} = 2.7 V	-	0.02	0.075	-	0.1	Ω
R _{ON(flat)}	ON resistance (flatness)	V _I = GND to V _{CC} ; I _{SW} = 100 mA							
			V _{CC} = 1.4 V	-	1.0	3.3	-	3.6	Ω
			V _{CC} = 1.65 V	-	0.5	1.2	-	1.3	Ω
			V _{CC} = 2.3 V	-	0.15	0.3	-	0.35	Ω
			V _{CC} = 2.7 V	-	0.13	0.3	-	0.35	Ω

[1] Typical values are measured at T_{amb} = 25 °C.

[2] Measured at identical V_{CC}, temperature and input voltage.

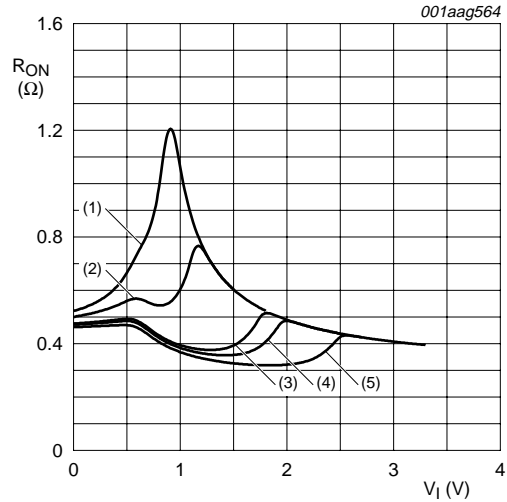
[3] Flatness is defined as the difference between the maximum and minimum value of ON resistance measured at identical V_{CC} and temperature.

11.3 ON resistance test circuit and graphs



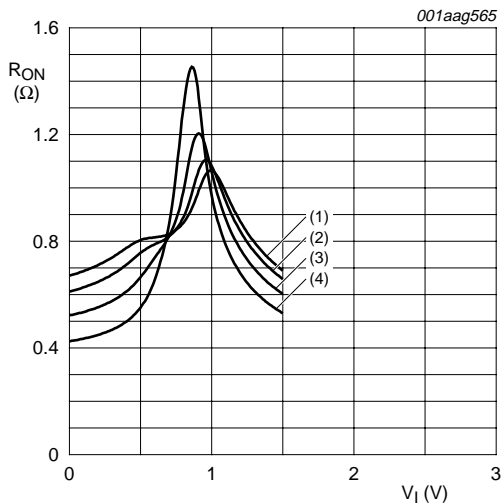
$R_{ON} = V_{SW} / I_{SW}$.

Fig 7. Test circuit for measuring ON resistance



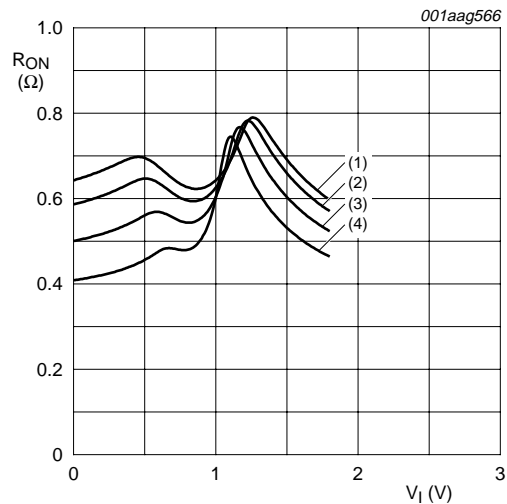
- (1) $V_{CC} = 1.5\text{ V}$.
 - (2) $V_{CC} = 1.8\text{ V}$.
 - (3) $V_{CC} = 2.5\text{ V}$.
 - (4) $V_{CC} = 2.7\text{ V}$.
 - (5) $V_{CC} = 3.3\text{ V}$.
- Measured at $T_{amb} = 25\text{ }^\circ\text{C}$.

Fig 8. Typical ON resistance as a function of input voltage



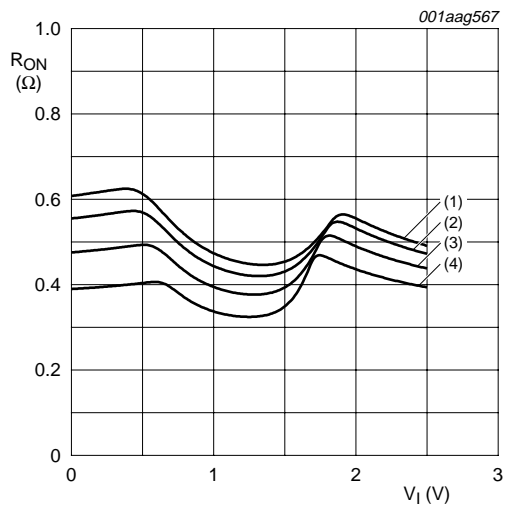
- (1) $T_{amb} = 125\text{ }^\circ\text{C}$.
- (2) $T_{amb} = 85\text{ }^\circ\text{C}$.
- (3) $T_{amb} = 25\text{ }^\circ\text{C}$.
- (4) $T_{amb} = -40\text{ }^\circ\text{C}$.

Fig 9. ON resistance as a function of input voltage; $V_{CC} = 1.5\text{ V}$



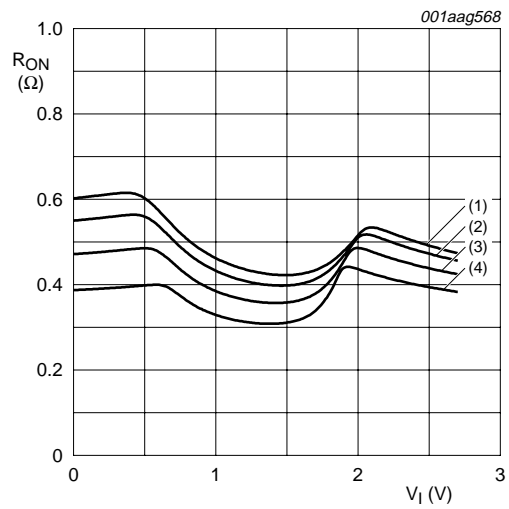
- (1) $T_{amb} = 125\text{ }^\circ\text{C}$.
- (2) $T_{amb} = 85\text{ }^\circ\text{C}$.
- (3) $T_{amb} = 25\text{ }^\circ\text{C}$.
- (4) $T_{amb} = -40\text{ }^\circ\text{C}$.

Fig 10. ON resistance as a function of input voltage; $V_{CC} = 1.8\text{ V}$



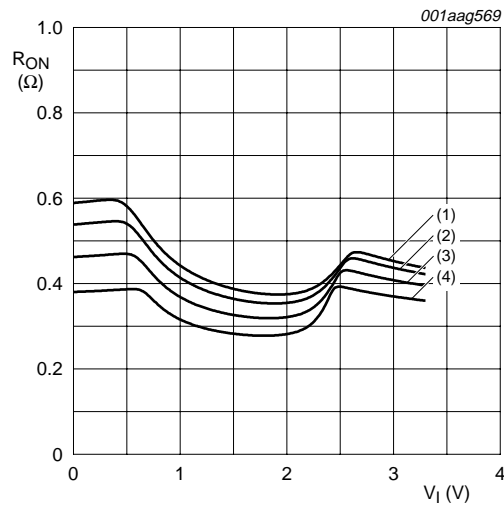
- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 11. ON resistance as a function of input voltage; $V_{CC} = 2.5\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 12. ON resistance as a function of input voltage; $V_{CC} = 2.7\text{ V}$



- (1) $T_{amb} = 125\text{ }^{\circ}\text{C}.$
- (2) $T_{amb} = 85\text{ }^{\circ}\text{C}.$
- (3) $T_{amb} = 25\text{ }^{\circ}\text{C}.$
- (4) $T_{amb} = -40\text{ }^{\circ}\text{C}.$

Fig 13. ON resistance as a function of input voltage; $V_{CC} = 3.3\text{ V}$

12. Dynamic characteristics

Table 9. Dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for load circuit see [Figure 15](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ ^[1]	Max	Min	Max (85 °C)	Max (125 °C)	
t _{en}	enable time	nE to nZ or nY; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	27.1	40	-	43	48	ns
		V _{CC} = 1.65 V to 1.95 V	-	22.1	27	-	34	36	ns
		V _{CC} = 2.3 V to 2.7 V	-	16.7	20	-	27	30	ns
t _{dis}	disable time	nE to nZ or nY; see Figure 14							
		V _{CC} = 1.4 V to 1.6 V	-	9.4	18	-	19	21	ns
		V _{CC} = 1.65 V to 1.95 V	-	6.6	13	-	14	15	ns
		V _{CC} = 2.3 V to 2.7 V	-	4.5	8	-	9	10	ns
		V _{CC} = 2.7 V to 3.6 V	-	3.8	8	-	8	9	ns

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.5 V, 1.8 V, 2.5 V and 3.3 V respectively.

12.1 Waveform and test circuits

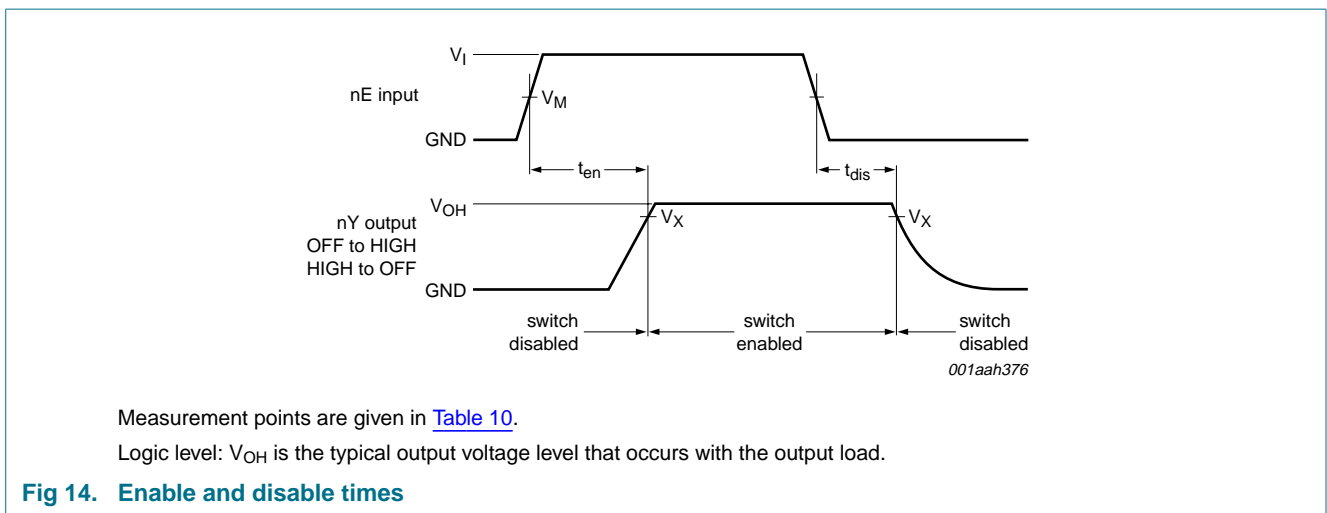


Table 10. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _X
1.4 V to 3.6 V	0.5V _{CC}	0.9V _{OH}

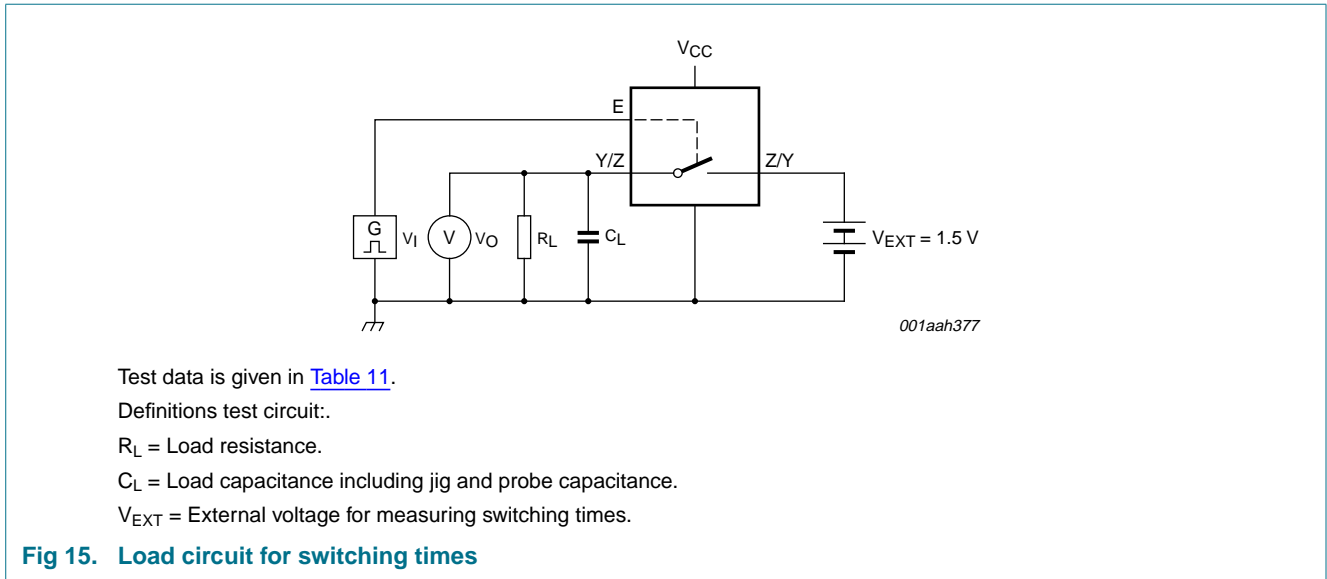


Table 11. Test data

Supply voltage	Input		Load	
V_{CC}	V_I	t_r, t_f	C_L	R_L
1.4 V to 3.6 V	V_{CC}	≤ 2.5 ns	35 pF	50 Ω

12.2 Additional dynamic characteristics

Table 12. Additional dynamic characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = GND$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5$ ns.

Symbol	Parameter	Conditions	25 °C			Unit
			Min	Typ	Max	
THD	total harmonic distortion	$f_i = 20$ Hz to 20 kHz; $R_L = 32 \Omega$; see Figure 16 ^[1]				
		$V_{CC} = 1.4$ V; $V_I = 1$ V (p-p)	-	0.15	-	%
		$V_{CC} = 1.65$ V; $V_I = 1.2$ V (p-p)	-	0.10	-	%
		$V_{CC} = 2.3$ V; $V_I = 1.5$ V (p-p)	-	0.015	-	%
		$V_{CC} = 2.7$ V; $V_I = 2$ V (p-p)	-	0.024	-	%
$f_{(-3dB)}$	-3 dB frequency response	$R_L = 50 \Omega$; see Figure 17 ^[1] $V_{CC} = 1.4$ V to 3.6 V	-	60	-	MHz
α_{iso}	isolation (OFF-state)	$f_i = 100$ kHz; $R_L = 50 \Omega$; see Figure 18 ^[1] $V_{CC} = 1.4$ V to 3.6 V	-	-90	-	dB
V_{ct}	crosstalk voltage	between digital inputs and switch; $f_i = 1$ MHz; $C_L = 50$ pF; $R_L = 50 \Omega$; see Figure 19 $V_{CC} = 1.4$ V to 3.6 V	-	0.16	-	V
Xtalk	crosstalk	between switches; ^[1] $f_i = 100$ kHz; $R_L = 50 \Omega$; see Figure 20 $V_{CC} = 1.4$ V to 3.6 V	-	-90	-	dB

Table 12. Additional dynamic characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); $V_I = \text{GND}$ or V_{CC} (unless otherwise specified); $t_r = t_f \leq 2.5 \text{ ns}$.

Symbol	Parameter	Conditions	25 °C			Unit	
			Min	Typ	Max		
Q_{inj}	charge injection	$f_i = 1 \text{ MHz}$; $C_L = 0.1 \text{ nF}$; $R_L = 1 \text{ M}\Omega$; $V_{gen} = 0 \text{ V}$; $R_{gen} = 0 \Omega$; see Figure 21					
			$V_{CC} = 1.5 \text{ V}$	-	3	-	pC
			$V_{CC} = 1.8 \text{ V}$	-	3	-	pC
			$V_{CC} = 2.5 \text{ V}$	-	3	-	pC
		$V_{CC} = 3.3 \text{ V}$	-	3	-	pC	

[1] f_i is biased at $0.5V_{CC}$.

12.3 Test circuits

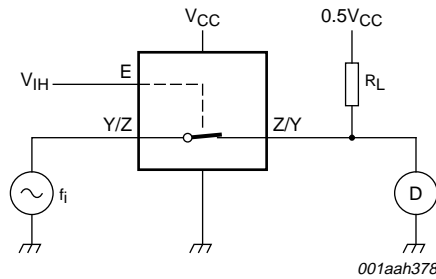
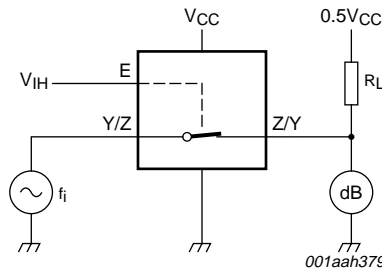
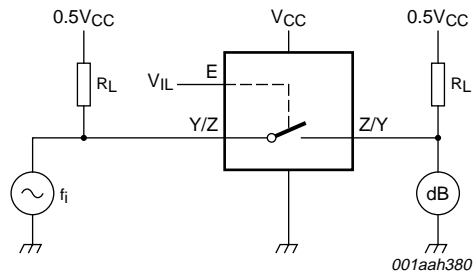


Fig 16. Test circuit for measuring total harmonic distortion



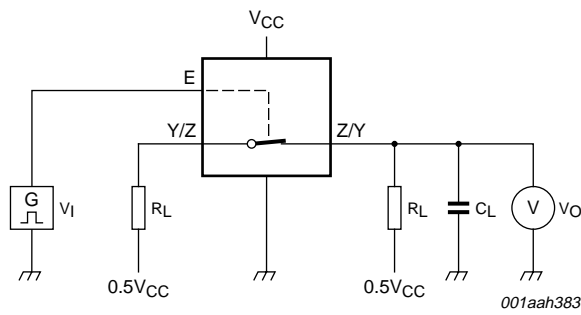
Adjust f_i voltage to obtain 0 dBm level at output. Increase f_i frequency until dB meter reads -3 dB.

Fig 17. Test circuit for measuring the frequency response when channel is in ON-state

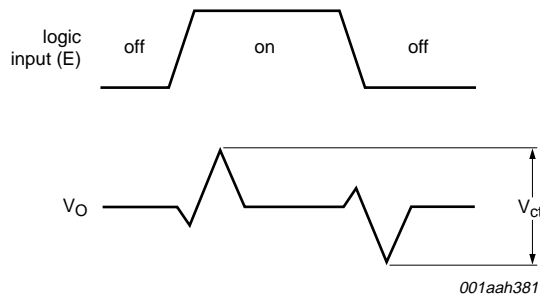


Adjust f_i voltage to obtain 0 dBm level at input.

Fig 18. Test circuit for measuring isolation (OFF-state)

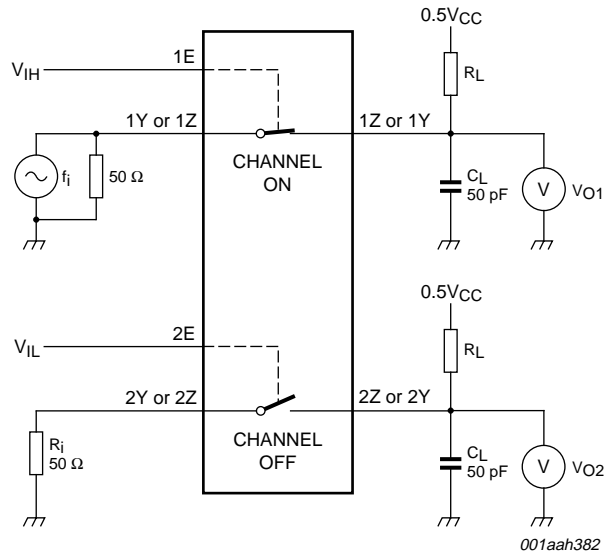


a. Test circuit



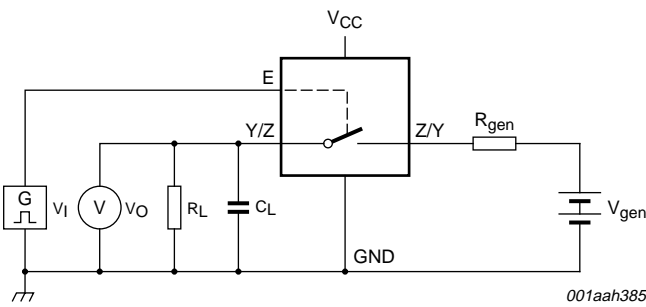
b. Input and output pulse definitions

Fig 19. Test circuit for measuring crosstalk voltage between digital inputs and switch

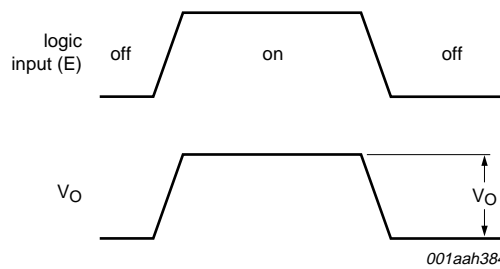


$20 \log_{10} (V_{O2} / V_{O1})$ or $20 \log_{10} (V_{O1} / V_{O2})$.

Fig 20. Test circuit for measuring crosstalk between switches



a. Test circuit



b. Input and output pulse definitions

Definition: $Q_{inj} = \Delta V_O \times C_L$.

ΔV_O = output voltage variation.

R_{gen} = generator resistance.

V_{gen} = generator voltage.

Fig 21. Test circuit for measuring charge injection

13. Package outline

XSON8: plastic extremely thin small outline package; no leads; 8 terminals; body 1 x 1.95 x 0.5 mm

SOT833-1

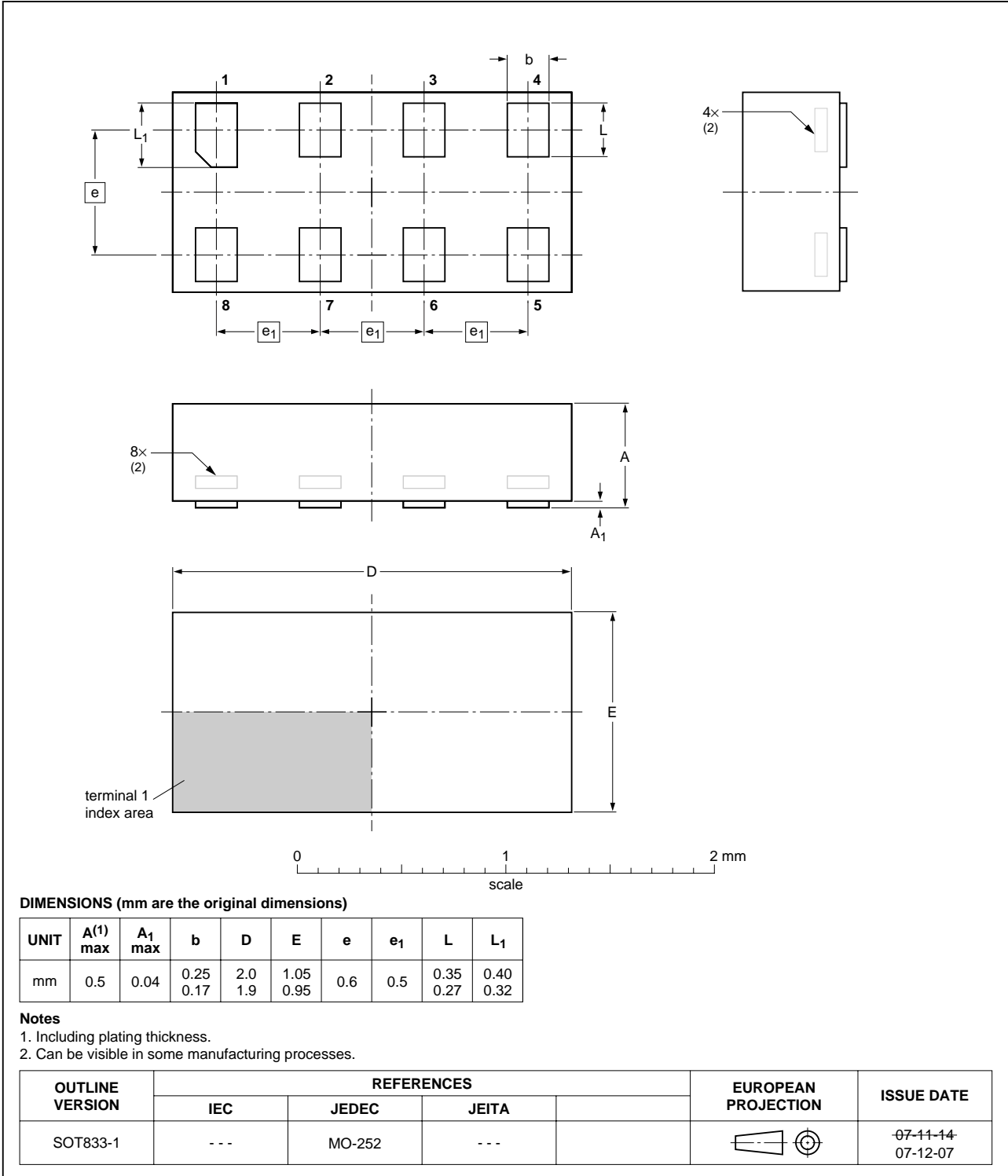


Fig 22. Package outline SOT833-1 (XSON8)

XQFN8U: plastic extremely thin quad flat package; no leads; 8 terminals; UTLP based; body 1.6 x 1.6 x 0.5 mm

SOT902-1

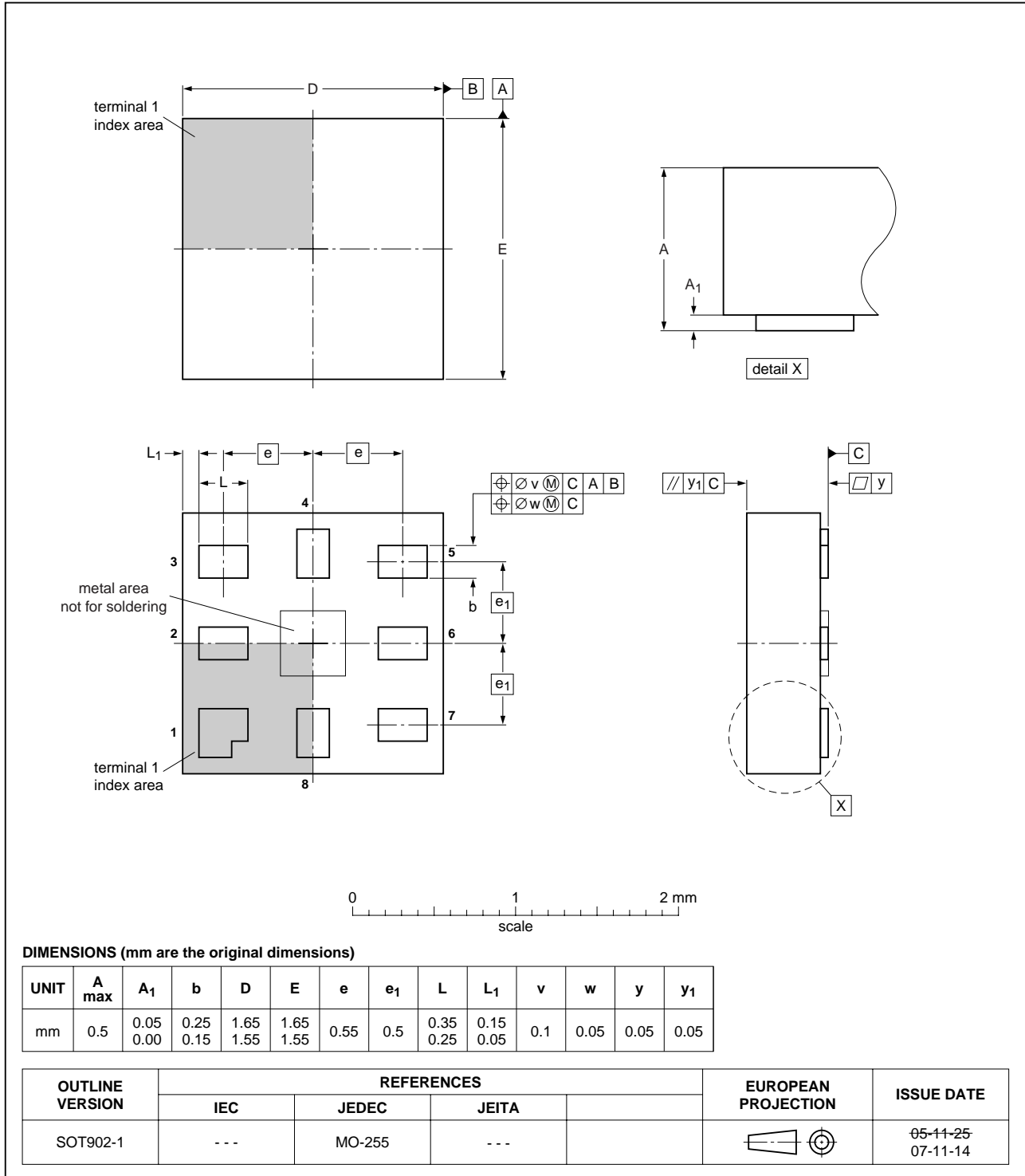


Fig 23. Package outline SOT902-1 (XQFN8U)

14. Abbreviations

Table 13. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3L2G66_1	20080131	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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